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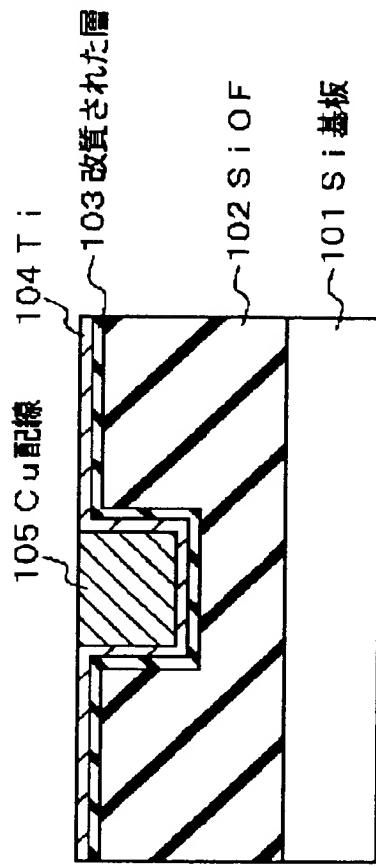
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APPLICANT : NEC CORP;

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TITLE : MANUFACTURE OF  
 SEMICONDUCTOR DEVICE



ABSTRACT : PROBLEM TO BE SOLVED: To enable avoidance of deterioration of an adhesion between an interlayer insulating film and a barrier metal or wiring layer, when a wiring groove is made in a silicon oxide film containing fluorine as the interlayer insulating film and the wiring layer is formed in the groove through a barrier metal of Ti, etc.

SOLUTION The manufacturing method includes steps of forming an SiOF film 102 on a substrate 101, forming an opening for wiring formation in the SiOF film, removing fluorine contained in the SiOF film from a surface of the opening, subjecting the fluorine-removed surface of the opening to an oxygen plasma process, and providing wiring metals 104 and 105 to the opening.

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